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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/840,386	04/23/2001	Yoshihisa Matsubara	NEKA 18.612 2510		
26304	0,710,200			EXAMINER	
	IUCHIN ZAVIS ROS ON AVENUE	VINH, LAN			
	, NY 10022-2585	ART UNIT	PAPER NUMBER		
			1765		

DATE MAILED: 09/16/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)		
	To a Andley C	09/840,386	MATSUBARA ET AL.		
Office Action Summary		Examiner	Art Unit		
		Lan Vinh	1765		
The M	IAILING DATE of this communication app	ears on the cover sheet with the c	orrespondence address		
A SHORTEN THE MAILING - Extensions of tir after SIX (6) MC - If the period for - If NO period for - Failure to reply - Any reply receiv	ED STATUTORY PERIOD FOR REPLY BY DATE OF THIS COMMUNICATION. The may be available under the provisions of 37 CFR 1.13 INTHS from the mailing date of this communication. The reply specified above is less than thirty (30) days, a reply reply is specified above, the maximum statutory period we within the set or extended period for reply will, by statute, and by the Office later than three months after the mailing arm adjustment. See 37 CFR 1.704(b).	i6(a). In no event, however, may a reply be tin within the statutory minimum of thirty (30) day ill apply and will expire SIX (6) MONTHS from Cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication.		
l	onsive to communication(s) filed on 20 Ju	ul. 2004			
		· · · · · ·			
	/	s action is non-final.			
	this application is in condition for allowal in accordance with the practice under <i>E</i> laims	Ex parte Quayle, 1935 C.D. 11, 4	osecution as to the merits is 53 O.G. 213.		
4)⊠ Claim(s	s) <u>1,2 and 4-11</u> is/are pending in the app	olication.			
4a) Of the above claim(s) <u>4-11</u> is/are withdrawn from consideration.					
	5) Claim(s) is/are allowed.				
6)⊠ Claim(s	) <u>1 and 2</u> is/are rejected.				
7) Claim(s	) is/are objected to.				
8) Claim(s	) are subject to restriction and/or	election requirement.			
Application Pape	ers	·			
9) The spec	cification is objected to by the Examiner.				
10)☐ The drav	ving(s) filed on is/are: a)□ accept	ed or b)⊡ objected to by the Exar	niner.		
Applica	ant may not request that any objection to the	drawing(s) be held in abeyance. Se	ee 37 CFR 1.85(a).		
	osed drawing correction filed on		ved by the Examiner.		
	oved, corrected drawings are required in repl				
	or declaration is objected to by the Exa	miner.			
	U.S.C. §§ 119 and 120				
	13)⊠ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).				
	a)⊠ All b)□ Some * c)□ None of:				
	ertified copies of the priority documents				
	— — — — — — — — — — — — — — — — — — —				
1	<ul> <li>3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).</li> <li>* See the attached detailed Office action for a list of the certified copies not received.</li> </ul>				
	dgment is made of a claim for domestic				
a) 🗌 The	translation of the foreign language provi	isional application has been rece	eived.		
15) ☐ Acknowle	dgment is made of a claim for domestic	priority under 35 U.S.C. §§ 120	and/or 121.		
Attachment(s)					
1) Notice of Refere 2) Notice of Draftsp 3) Information Disc	nces Cited (PTO-892) person's Patent Drawing Review (PTO-948) dosure Statement(s) (PTO-1449) Paper No(s)	5) Notice of Informal Pa	(PTO-413) Paper No(s) atent Application (PTO-152)		
J.S. Patent and Trademark Office PTO-326 (Rev. 04-01)		on Summary F	Part of Paper No. 091404		

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#### **DETAILED ACTION**

### Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 7/20/2004 has been entered.

#### Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.
- 3. Claim 1 is rejected under 35 U.S.C. 102(e) as being anticipated by Miyawaki et al (US 5,952,694).

Miyawaki discloses a method for manufacturing a semiconductor device. This method comprises the steps of:

forming N-type region and P-type region on a substrate (col 8, lines 63-64), forming electrode 30/wiring to connect the N and P-type region (col 9, lines 6-8; fig. 10)

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performing a cleaning step/processing step on the semiconductor substrate (col 20, lines 45-46), applying an etching solution/liquid to the semiconductor substrate to expose the wiring (col 20, lines 65-67, fig. 36), applying a He-Ne laser/light source on the upper surface of the semiconductor substrate (col 21, lines 32-34), the He-Se laser having a wavelength of 600 nm (col 8, lines 54-55), which overlaps the claimed range of 500 nm to less than 1 microns

Miyawaki also discloses performing the cleaning step after polishing the semiconductor substrate (col 13, lines 40-42)

Since the method of Miyawaki uses the same steps and a light source having the same wavelength as that of the claimed invention, then under the principle of inherency using the light source in the method of Miyawaki would inherently reduce an electromotive force at a PN junction in said semiconductor substrate, thereby inhibiting galvanic effect due to photo excitation before, during or after the step including CMP, and preventing oxidation of a surface of said wiring.

# Claim Rejections - 35 USC § 103

- 4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 5. Claim 2 is rejected under 35 U.S.C. 103(a) as being unpatentable over Miyawaki et al (US 5,952,694) in view of Klebanoff (US 6,169, 652)

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Miyawaki's method has been described above. Unlike the instant claimed invention as per claim 2, Miyawaki fails to disclose that the processing/cleaning step is performed in a state in which the semiconductor substrate is grounded.

However, Klebanoff, in a method of using different chucks to hold semiconductor wafer during processing, teaches maintaining/controlling the semiconductor substrate at zero voltage (ground potential) during processing (col 3, lines 15-17)

Since both Miyawaki and Klebanoff are concerned with the step of cleaning the semiconductor substrate, one skilled in the art would have found it obvious to modify Miyawaki method by maintaining/controlling the semiconductor substrate at zero voltage (ground potential) during processing as per Klebanoff because Klebanoff states that employing a voltage-controlled electrostatic chuck will significantly reduce the likelihood of contaminant deposition on the substrate (see abstract).

## Response to Arguments

6. Applicant's arguments with respect to claims 1-2 have been considered but are moot in view of the new ground(s) of rejection.

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### Conclusion

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7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lan Vinh whose telephone number is 571 272 1471. The examiner can normally be reached on M-F 8:30-5:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571 272 1465. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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September 15, 2004